



°C		

	°C			
				°C
				°C



	°C					
	°C					
	°C					

°C

			±		

FIG 1: Power dissipation vs. gate current (per thyristor or diode)

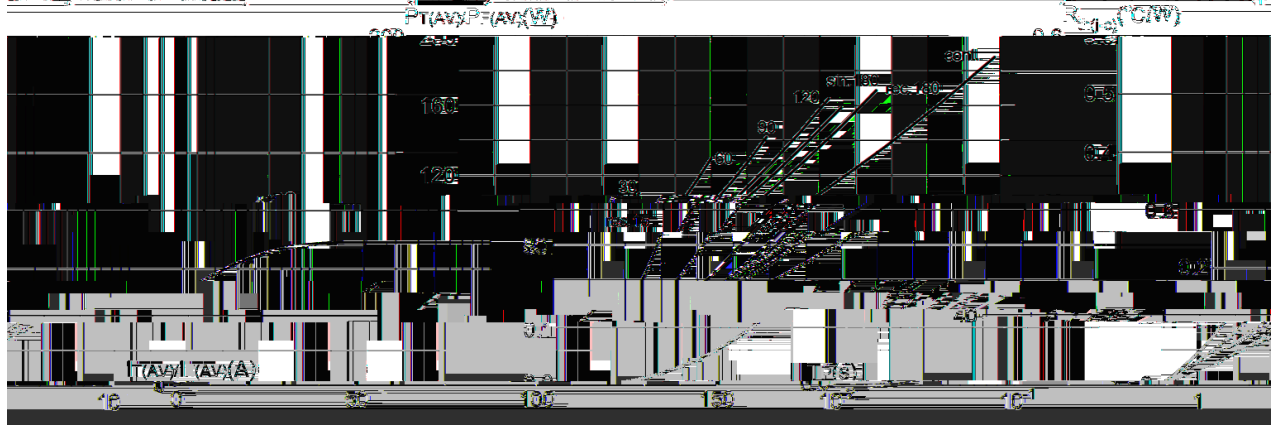


FIG 2: Maximum transient thermal impedance junction to case(per thyristor or diode)

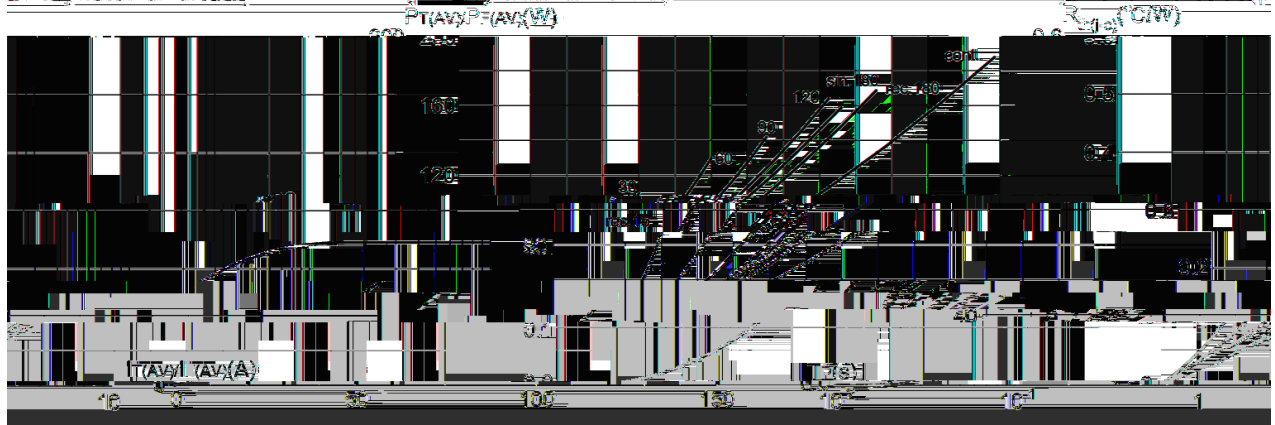


FIG 3: Forward current vs. case temperature

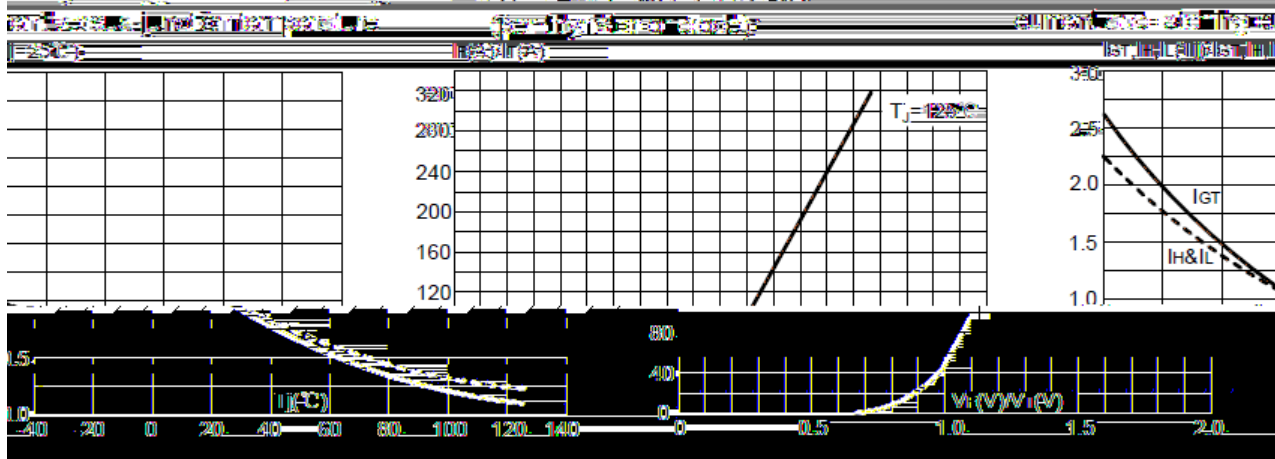


FIG 4: Relative variations of gate trigger current, holding current and break over voltage

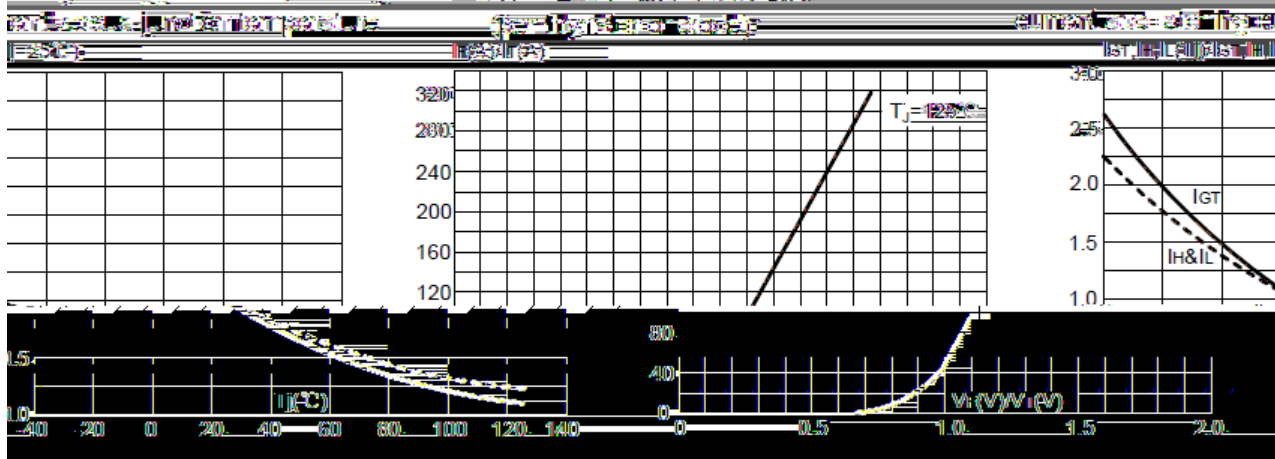


FIG 5: Gate trigger characteristics

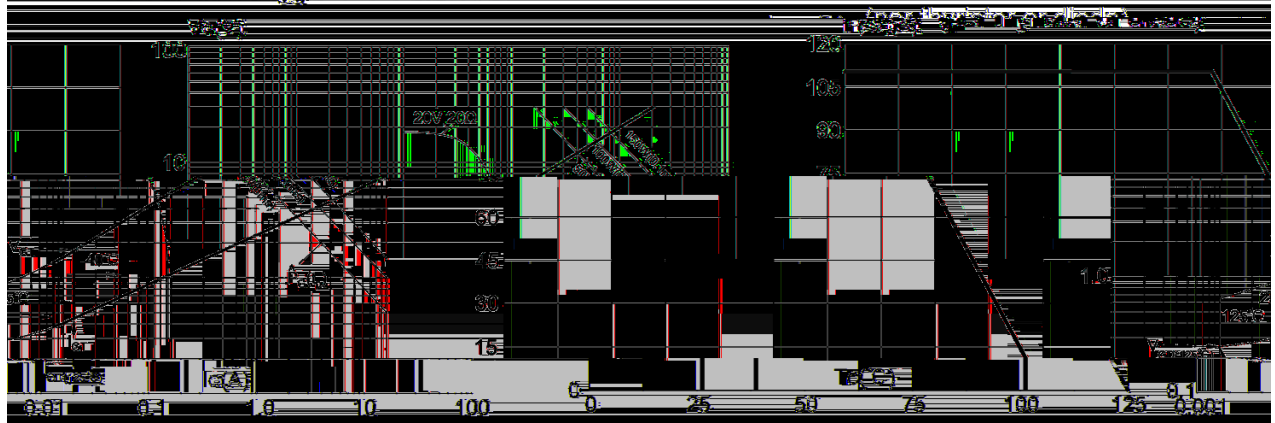


FIG 6: Forward current vs. case temperature

